Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	. 1	"20050212087"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/25 19:52
S2		akatsu-hiroyuki.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:06
S3	73	divakaruni-rama.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:06
S4	3	khater-marwan.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON .	2005/11/11 17:06
S5	4	schnabel-christopher-m.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:07
S6	8	tonti-william.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:07
S7	137	S2 S3 S4 S5 S6	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:07
S8	` 6	S7 and (bipolar adj transistor) and \$4capacitanc\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:07
S9	12	("20030057458" "20030109109" "4994400" "5128271" "5494836" "5506427" "5962880" "6346453" "6548882" "6586782" "6777782" "6806554").PN.	US-PGPUB; USPAT; USOCR	OR	ON .	2005/11/11 17:17
S10	4322	(bipolar adj transistor) and ((dielectric or insulat\$3) with (void or hole or gap or cave or empty)) .	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:47
S11	2791	S10 and (\$4capacit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR .	ON	2005/11/11 17:25
\$12	116	S11 and (intrinsic and extrinsic) adj2 base	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:25
S13	30	S12 and ("STI" or (trench near2 isolat\$3))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:27

S14	29	S13 not S7	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:27
S15	13	S14 and ((dielectric or insulat\$3) with (void or gap or cave or empty))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:41
S16	5	(S12 not S15) and (air near2 (gap or void or hole))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:43
S17	169	(S11 not (S7 S13 S15)) and (air near2 (gap or void or hole))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:48
S18	4	S17 and (intrinsic adj2 base)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR .	ON	2005/11/11 17:44
S19	125	(bipolar adj transistor) and ((dielectric or insulat\$3) with ((void or hole or gap or cave or empty) near2 air))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:48
S20	120	S19 not (S7 S13 S15 S16 S18)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:05
S21	40	S20 and (base and collector and emitter)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 10:26
S22	. 80	S20 not S21	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 17:58
S23	4	10/249299	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON ·	2005/11/11 17:56
S24	1103	(bipolar adj transistor) and base and (collector same ((dielectric or insulat\$3 or \$3oxide) with (void or cave or gap or hole)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:42
S25	21	S24 and (air near3 (void or cave or gap or hole))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:05
S26	13	S25 not (S7 S13 S15 S16 S18 S21 S22 S23)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:07

		•				
S27	1068	(S24 not (S7 S13 S15 S16 S18 S21 S22 S23 S26))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:07
S28	434	S27 and ((reduc\$4 or decreas\$3 or low\$4) with capacit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:08
S29	39	S28 and ((void or gap or hole or cave) with (reduc\$4 or decreas\$3 or low\$4) with capacit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:31
S30	7	"5668396"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:46
S31	2	S24 and ((void or cave or gap or hole) near2 vacuum)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 18:42
S32	11	"5798561"	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 19:15
S33	12	("0057458" "0109109" "5798561" "5930635" "5962880" "512827 1" "5494836" "5506427" "5962880" "6940149" "6346453").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2005/11/11 19:16
S34	551	emitter and (collector same (air with (gap or hole or void)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:56
S35	36	S34 and ((insulat\$4 or \$2oxide\$2 or insulat\$4) with (air with (hole or void or gap)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:30
S36	24	S35 and (@ad<"20040329" or @rlad<"20040329")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/02 16:00
S37	13	(US-20050212087-\$ or US-20050199907-\$ or US-20020058388-\$).did. or (US-6762447-\$ or US-5494836-\$ or US-6940149-\$ or US-5962880-\$ or US-6462397-\$ or US-6380017-\$ or US-6642553-\$ or US-6482710-\$ or US-5798561-\$ or US-6114744-\$).did.	US-PGPUB; USPAT	OR	ON	2006/06/01 19:31
S38	130	·	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:41
S39	39	S38 and (collector with (air near3 (gap or hole or void)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:44

S40	26	(S38 not S39) and (bipolar with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 20:18
S41	0	(S38 not (S39 S40)) and (intrinsic with base)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:47
S42	65	(S38 not (S39 S40))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:54
S44	1386	257/522,e21.573,e21.581.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:55
S45	169	438/318, "319,421".ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/02 17:31
S46	9	(S44 S45) and (collector same (air with (gap or hole or void or groove or slot)))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 19:56
S47	11	(S34 not (S35 S36 S37 S38)) and (bipolar with transistor)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 20:19
S48	2	("4196440" "4685198").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/06/01 20:46
S49	0	("6964907"),URPN.	USPAT	OR	ON	2006/06/01 20:47
S51	1	(collector and (intrinsic adj base) and \$5capacit\$4 and (void or gap or hole or groove or slot) and emitter and (raised adj2 base)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 20:59
S52	18	(collector and (intrinsic adj base) and \$5capacit\$4 and (void or gap or hole or groove or slot) and emitter and (raised adj2 base))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 21:13
S53	26	(collector and (intrinsic adj base) and (void or gap or hole or groove or slot) and emitter and (raised adj2 base)) and (@ad<"20040329" or @rlad<"20040329")	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 21:14
S54	. 11	S53 not (S35 S36 S37 S38 S46 S47 S48 S51 S52)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/01 21:14
S55	414	collector and (emitter same (extrinsic adj base) same spacer)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/06/02 16:01

S56 S58 Solector and territors ame textinistic adj base) same (spacer or sidewall or (side adj wall)) SPAT: USPAT: USCAT: USCAT							
adj (spacer or sidewall or (side adj wall)) USPAT; USOCR; EPO, IPO; IBM_TIDB USPAGPUB; USP	S56	638		USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:26
S59 35 S57 not S58	S57	57	S56 and (@ad<"20040329" or @rlad<"20040329") and (second adj (spacer or sidewall or (side adj wall)))	USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:34
S60 262 (S56 not S57) and ((intrinsic adj base) with (\$30xide or insulat\$4 or dielectric or isolat\$4)) USPAT; USCOR; EPC, JPO; IBM_TDB US_PGPUB; US_PAT; USCOR; EPC, JPO; IBM_TDB US_PGPUB; US_PGPUB; US_PGPUB; US_PAT; USCOR; EPC, JPO; IBM_TDB US_PGPUB; US_PGPUB; US_PAT; USCOR; EPC, JPO; IBM_TDB US_PGPUB; US_PAT; USCOR; EPC, JPO; DERWENT; IBM_TDB US_PGPUB; USCOR; EPC, JPO; DERWENT; IBM_TDB US_PGPUB; US_PAT; USCOR; EPC, JPO; USCOR; EPC, JPO	S58	22	S57 and (subcollector or (sub adj collector))	USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:23
Second S	S59	35	S57 not S58	USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:23
Solution	S60	262		USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:29
S62	S61	240		USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:28
S64 31 S62 and ((second or inner or outer or another) adj3 (spacer or sidewall or (side adj wall))) USPAT; USOCR; EPO; JPO; IBM_TDB USPAT; USOCR; EPO; JPO; DERWENT;	S62	130	or over\$3 or overla\$3 or atop or beneath or below or on) with	USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:32
Sidewall or (side adj wall)))	S63	1		USPAT; USOCR; EPO; JPO;	OR	ON .	2006/06/02 16:33
S65 S69 438/318,319,421.ccls.	S64	31		USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 16:35
S66 381 257/522.ccls.	S65	569	438/318,319,421.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	ON	2006/06/02 17:31
S67 1381 257/565.ccls. US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	S66	381	257/522.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2006/10/26 10:25
	S67	1381	257/565.ccls	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	ON	2006/10/25 19:54
	S68	0	("2006/0097351").URPN.		OR	ON	2006/10/25 20:02

		_				
S69	4304	257/522,557,517,521,524,588,565,e23.013,e21.573,e21.581. ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/26 10:26
S70	1058	438/318,319,322,335,312.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/26 10:26
S71	2506	(S69 S70) and (base and collector and emitter)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 10:27
S72	2044	S71 and (dop\$4 implant\$3 implantat\$3 concentrat\$4 density dose dosage) and (dielectric insulat\$3 \$20xide capacit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 10:59
S73	69	S72 and ((void gap space cavity trench) with (vacuum evacuat\$4 gas))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 10:30
S74	108	S72 and ((void gap space cavity trench) with (vacuum evacuat\$4 gas air))	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 11:07
S75	91	S74 and (epi\$4 epitaxi\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 11:00
S76	0	("2004/0262715").URPN	USPAT	OR	ON	2006/10/26 10:53
S77	2455	(base and collector and emitter and (dop\$4 implant\$3 implantat\$3 concentrat\$4 density dose dosage) and (dielectric insulat\$3 \$20xide capacit\$4)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 11:02
S78	837	S77 and (epi\$4 epitaxi\$4).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 11:00
S79	254	S78 and ((dop\$4 implant\$3 implantat\$3) with (concentrat\$4 density dose dosage)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 11:03
S80	0	S79 and (undercut\$3 (under adj2 cut\$3)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 11:01
S82	63	S79 and ((high large low small) same (dop\$4 implant\$3 implantat\$3) same (concentrat\$4 density dose dosage)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/10/26 11:04

S83	1	S78 and ((void gap space cavity trench) with (vacuum evacuat\$4 gas air)).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; IBM_TDB	OR	ON	2006/10/26 11:07
S84	25	(US-20020153535-\$ or US-20020197808-\$ or US-20030057458-\$ or US-20040012036-\$ or US-20050079658-\$ or US-20050116254-\$ or US-20050184359-\$ or US-20050199907-\$ or US-20050212087-\$).did. or (US-5318916-\$ or US-5648666-\$ or US-5266819-\$ or US-4949145-\$ or US-5656514-\$ or US-5289020-\$ or US-5468659-\$ or US-6444535-\$ or US-6531720-\$ or US-6534802-\$ or US-6774411-\$ or US-6888180-\$ or US-6924202-\$ or US-6927476-\$ or US-6940149-\$ or US-6972237-\$).did.	US-PGPUB; USPAT	OR	ON	2006/10/26 11:09